

IN THE SPECIFICATION

Please amend the paragraph(s) extending from page 2, line 30 through page 3, line 6 as follows:

- A disclosed method for forming a fine pattern comprises:
- (a) coating an etching mask layer on an underlying layer;
 - (b) coating a photoresist film ~~capable absorbing gas generated from the photoresist film composition including silicon~~ on the etching mask layer to form a photoresist film;
 - (c) coating a gas protection film on the photoresist film;
 - (d) performing a photolithography process on the resulting structure to form a photoresist film pattern;
 - (e) etching the etching mask layer of the step (b) using the photoresist film pattern as an etching mask to form an etching mask pattern; and
 - (f) forming an underlying layer pattern by an etching process using the etching mask pattern.

Please amend the paragraph beginning on page 3, line 10 as follows:

Preferably, the photoresist film used in the step (b) is one of the photoresist[[s]] films suitable for a photolithographic process employing light sources such as [[for]] ArF (193nm), VUV (157nm) or EUV (13nm) ~~including silicon~~.